Clean copy, pursuant to 37 C.F.R. § 1.121(b)(1)(ii), of the paragraph amended at page 2 of the specification:

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This is a divisional application of US Patent Application Serial No. 08/846,671, filed on April 30, 1997, titled "UNDOPED SILICON DIOXIDE AS ETCH STOP FOR SELECTIVE ETCH OF DOPED SILICON DIOXIDE", which is incorporated herein by reference.

Marked-up copy, pursuant to 37 C.F.R. § 1.121(b)(1)(iii), of the paragraph amended at page 2 of the specification:

This is a divisional application of US Patent Application Serial No. 08/846,671, filed on April [20]30, 1997, titled "UNDOPED SILICON DIOXIDE AS ETCH STOP FOR SELECTIVE ETCH OF DOPED SILICON DIOXIDE", which is incorporated herein by reference.